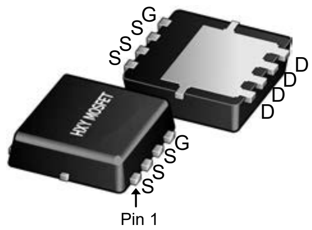
SIS402DN-T1-GE3

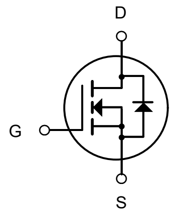
N-Channel Enhancement Mode MOSFET

Description

The SIS402DN-T1-GE3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN3X3-8L
(PowerPAK1212-8)



N-Channel MOSFET

General Features

V_{DS} = 30V I_D =80 A

$R_{DS(ON)}$ < 6 mΩ @ V_{GS}=10V

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SIS402DN-T1-GE3	DFN3X3-8L (PowerPAK1212-8)	HXY MOSFET	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	30	V
VGS	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	80	A
I_D@T_C=100˚C	Continuous Drain Current, V_{GS} @ 10V[1]	50	A
IDM	Pulsed Drain Current[2]	162	A
EAS	Single Pulse Avalanche Energy[3]	144.7	mJ
IAS	Avalanche Current	53.8	A
P_D@T_C=25˚C	Total Power Dissipation[4]	62.5	W
TSTG	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C
$R_{\theta}JA$	Thermal Resistance Junction-ambient [1]	62	˚C/W
$R_{\theta}JC$	Thermal Resistance Junction-Case[1]	2.4	˚C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.0213	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=30A	---	4.7	6	mΩ
		V_{GS}=4.5V , I_D=15A	---	5.9	8	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	1.5	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.73	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=30A	---	26.5	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.4	2.8	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=15A	---	31.6	---	nC
Q_{gs}	Gate-Source Charge		---	8.6	---	
Q_{gd}	Gate-Drain Charge		---	11.7	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω I_D=15A	---	9	---	ns
T_r	Rise Time		---	19	---	
$T_{d(off)}$	Turn-Off Delay Time		---	58	---	
T_f	Fall Time		---	15.2	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	3075	4000	pF
C_{oss}	Output Capacitance		---	400	530	
C_{rss}	Reverse Transfer Capacitance		---	315	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	80	A
I_{SM}	Pulsed Source Current[2,5]		---	---	162	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	IF=30A , dI/dt=100A/µs , T_J=25℃	---	18	---	nS
Q_{rr}	Reverse Recovery Charge		---	8	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=53.8A
4.The power dissipation is limited by 175℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

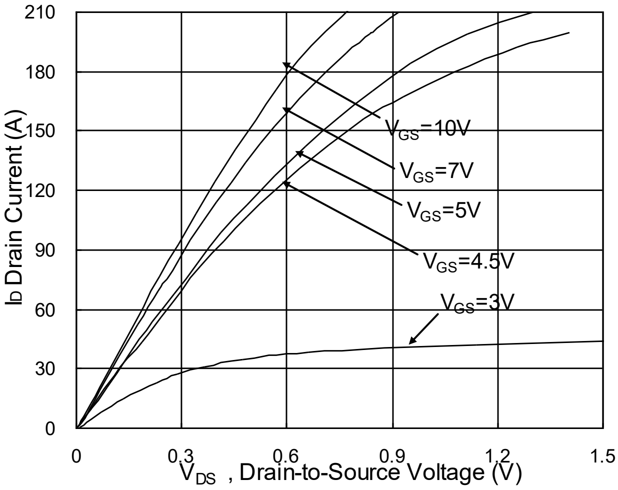


Fig.1 Typical Output Characteristics

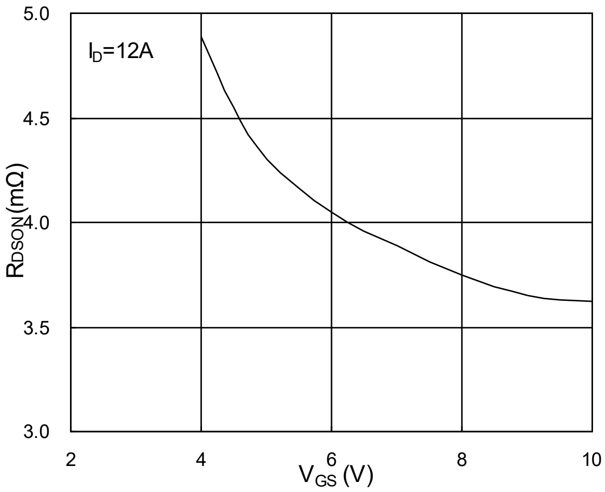


Fig.2 On-Resistance vs. G-S Voltage

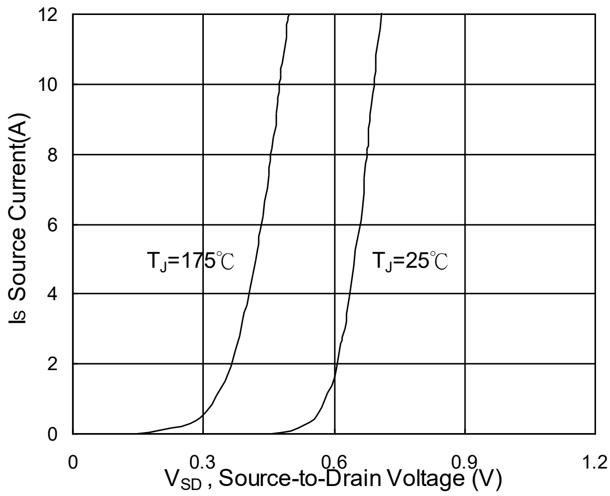


Fig.3 Forward Characteristics of Reverse

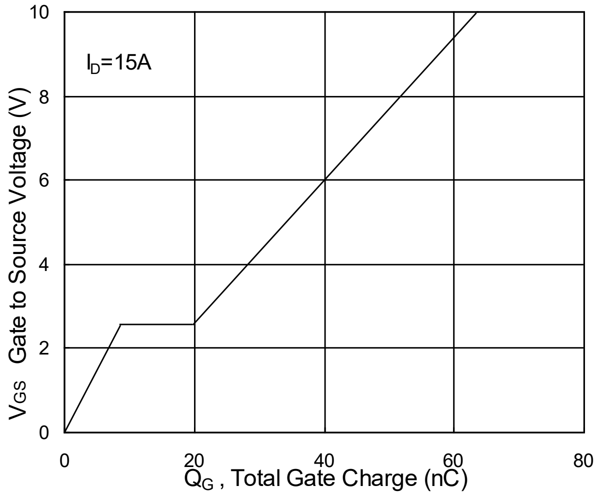


Fig.4 Gate-Charge Characteristics

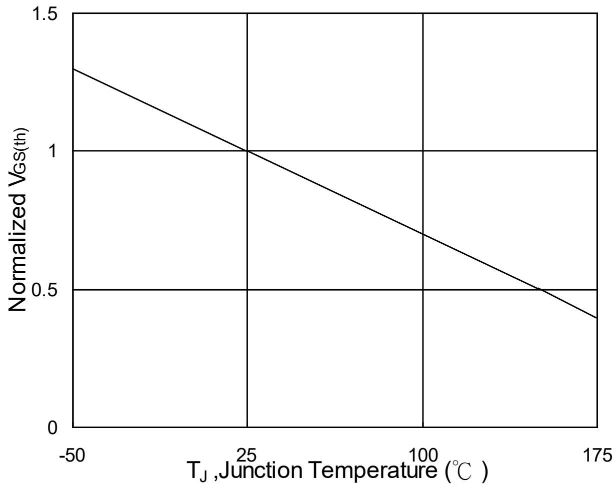


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

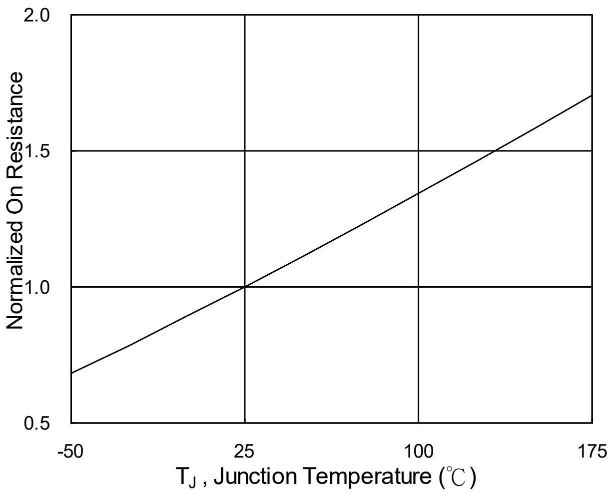


Fig.6 Normalized R_{DSON} vs. T_J

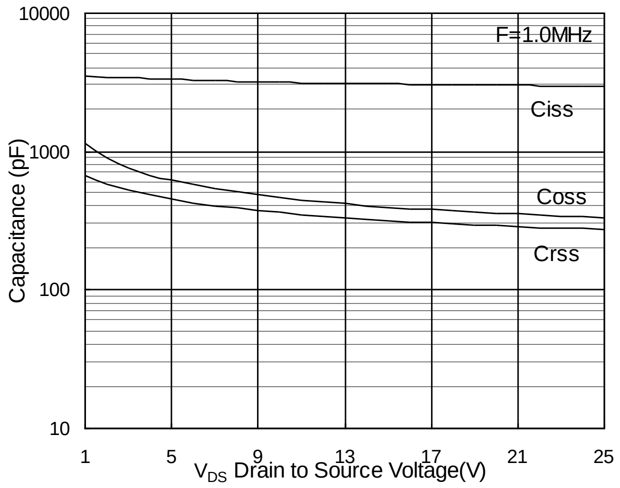


Fig.7 Capacitance

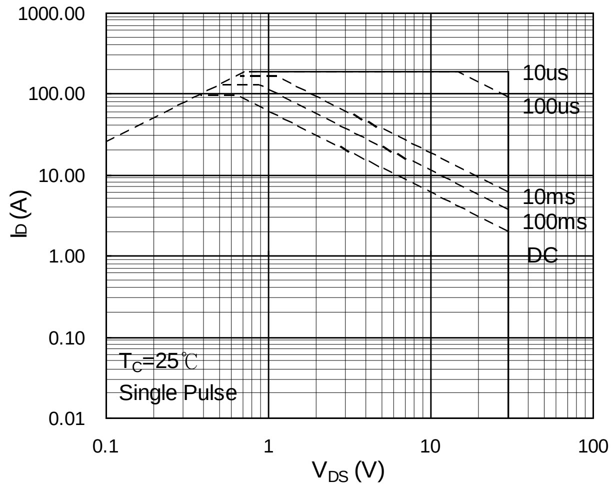


Fig.8 Safe Operating Area

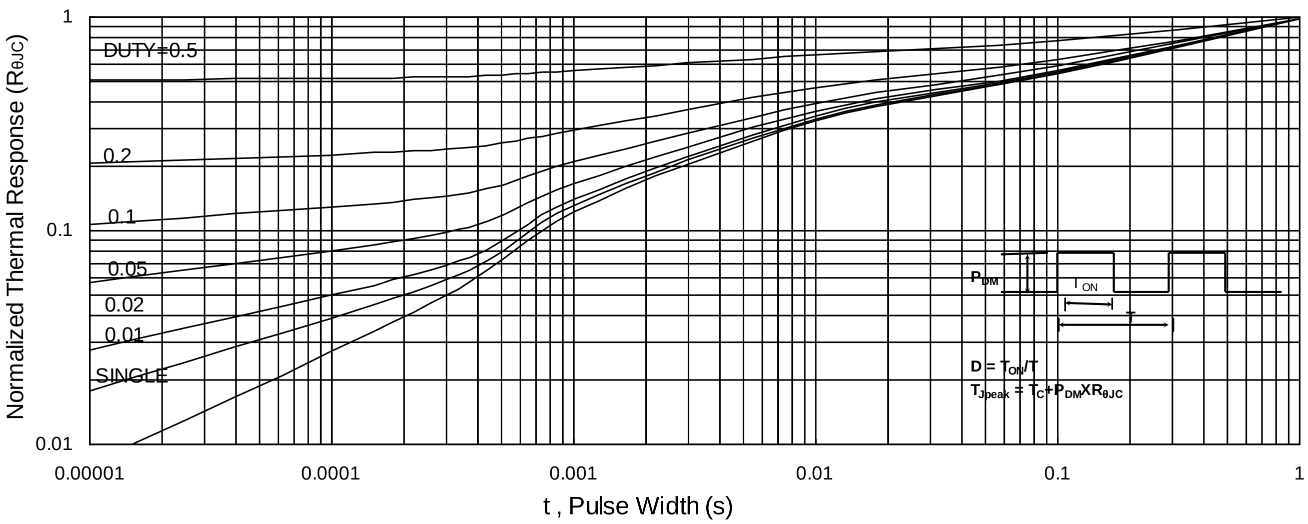


Fig.9 Normalized Maximum Transient Thermal Impedance

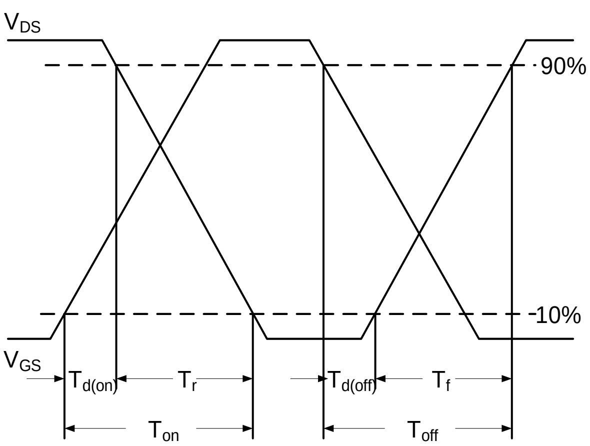


Fig.10 Switching Time Waveform

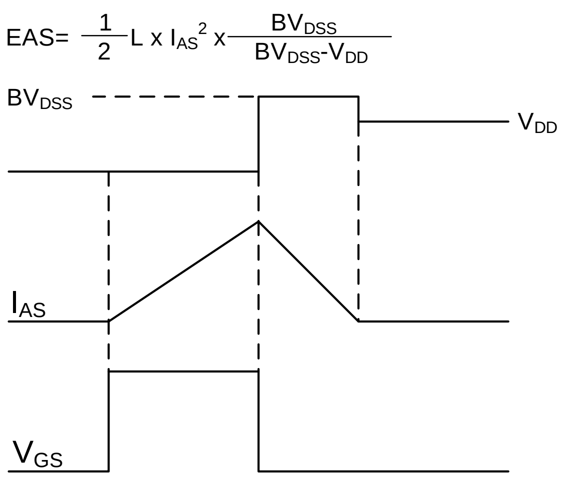
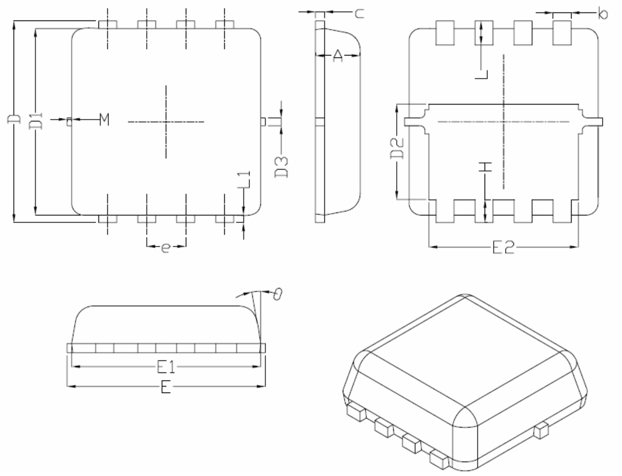


Fig.11 Unclamped Inductive Switching Waveform

DFN3X3-8L(PowerPAK1212-8) Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

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